CCM1095 20 TO 1000 MHz HIGH POWER AMPLIFIER

Typical Values	*CCM1095*
High Output Power	*+38 dBm*
Broad Bandwidth	*20-1000 MHz*
High Third Order I.P.	*+49 dBm*

High Performance Thin Film for RF Section
Includes Bias Sequencer

SPECIFICATIONS*

Parameter	Typical	Guaranteed 0 to 50° C	Guaranteed -55 to +85° C
Frequency (Min.)	**10-1200 MHz**	**20-1000 MHz**	**20-1000 MHz**
Small Signal Gain (Min.)	11.3 dB	10.5 dB	10.0 dB
Gain Flatness (Max.)	±0.5 dB	±0.7 dB	±0.8 dB
Noise Figure (Max.)			
50-100 MHz	4.5 dB	5.2 dB	5.7 dB
100-1000 MHz	4.0 dB	4.7 dB	5.2 dB
SWR (Max.) Input/Output	1.7:1	2.0:1	2.0:1
Power Output (Min.)^			
@ 1dB comp. 20-70 MHz	+37.0 dBm	+36.0 dBm	+35.5 dBm
70-1000 MHz	+38.0 dBm	+37.0 dBm	+36.5 dBm
Reverse Isolation	18.0 dB	—	—
DC Current (Max.)	500 mA	520 mA	530 mA

* Measured in a 50-ohm system at +36 Vdc unless otherwise specified.
^ Output Power averages 1.5 dBm less using +28 Vdc.

INTERMODULATION PERFORMANCE

Typical @ 25° C	*+28 Volts*	*+36 Volts*
Second Order Harmonic Intercept Point	+66 dBm	+64 dBm
Second Order Two Tone Intercept Point	+60 dBm	+58 dBm
Third Order Two Tone Intercept Point	+48 dBm	+49 dBm

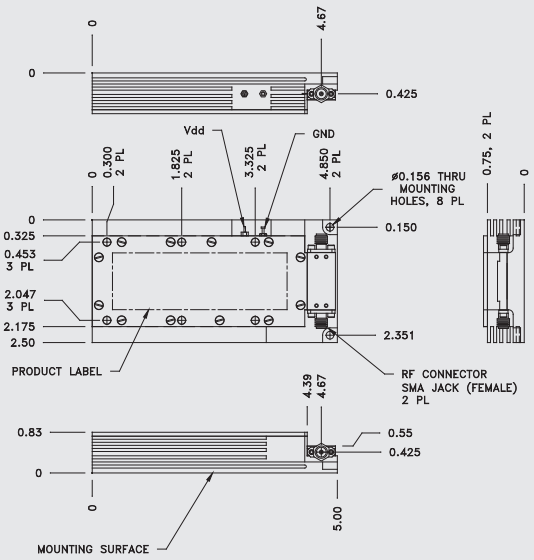
ABSOLUTE MAXIMUM RATINGS

Storage Temperature	-65 to 150° C
Maximum Case Temperature	+125° C
Maximum DC Voltage	+40 Volts
Maximum Continuous RF Input Power	+30 dBm
Maximum Short Term Input Power (1 Minute Max.)	+33 dBm
Maximum Peak Power (3 µsec Max.)	+35 dBm
Burn-in Temperature	105° C
Thermal Resistance[1] (θjc)	+5 C/Watt
Junction Temperature Rise Above Case (Tjc) **+28 V**	+70° C
+36 V	+90° C

[1] Thermal resistance is based on total power dissipation.

CCM1095

Power Amplifier, SMA with Sequencer



Vdd = +28/+36 V

DIMENSIONS ARE IN INCHES (MILLIMETERS)

TYPICAL PERFORMANCE